Ivan G Ivanov

List of Publications by Year in descending order

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211	4,253	126907	161849
papers	citations	33 h-index	54 g-index

214	214	214	3955
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Vibrational properties and structure of undoped and Al-doped ZnO films deposited by RF magnetron sputtering. Thin Solid Films, 2000, 379, 28-36.	1.8	228
2	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. Nature Communications, 2019, 10, 1954.	12.8	167
3	Annealing effects on optical properties of low temperature grown ZnO nanorod arrays. Journal of Applied Physics, 2009, 105, .	2.5	123
4	Growth of SiC by ?Hot-Wall? CVD and HTCVD. Physica Status Solidi (B): Basic Research, 1997, 202, 321-334.	1.5	121
5	High temperature chemical vapor deposition of SiC. Applied Physics Letters, 1996, 69, 1456-1458.	3.3	111
6	Developing silicon carbide for quantum spintronics. Applied Physics Letters, 2020, 116, .	3.3	101
7	Nitrogen doping concentration as determined by photoluminescence in 4Hâ€“ and 6Hâ€“SiC. Journal of Applied Physics, 1996, 80, 3504-3508.	2.5	96
8	Quantum Properties of Dichroic Silicon Vacancies in Silicon Carbide. Physical Review Applied, 2018, 9, .	3.8	90
9	Properties of molecular-beam epitaxy-grown GaNAs from optical spectroscopy. Journal of Applied Physics, 1998, 84, 3830-3835.	2.5	83
10	Properties of theD1bound exciton in4Hâ^'SiC. Physical Review B, 1999, 59, 1956-1963.	3.2	80
11	Correlation between the antisite pair and theDIcenter in SiC. Physical Review B, 2003, 67, .	3.2	72
12	The influence of the substrate material on the growth of V2O5 flash-evaporated films. Applied Surface Science, 1995, 90, 389-391.	6.1	71
13	Extremely high quantum efficiency of donor-acceptor-pair emission in N-and-B-doped 6H-SiC. Journal of Applied Physics, 2006, 99, 093108.	2.5	67
14	Liquid phase epitaxial growth of SiC. Journal of Crystal Growth, 1999, 197, 147-154.	1.5	65
15	Photoluminescence of electron-irradiated4Hâ^'SiC. Physical Review B, 1999, 59, 8008-8014.	3.2	64
16	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. Nano Letters, 2019, 19, 7173-7180.	9.1	61
17	Growth of thick GaN layers with hydride vapour phase epitaxy. Journal of Crystal Growth, 2005, 281, 17-31.	1.5	55
18	Nanoscale phenomena ruling deposition and intercalation of AlN at the graphene/SiC interface. Nanoscale, 2020, 12, 19470-19476.	5.6	54

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19	Identification and tunable optical coherent control of transition-metal spins in silicon carbide. Npj Quantum Information, 2018, 4, .	6.7	53
20	Ionization energies of phosphorus and nitrogen donors and aluminum acceptors in4Hsilicon carbide from the donor-acceptor pair emission. Physical Review B, 2005, 71, .	3.2	48
21	Layer-number determination in graphene on SiC by reflectance mapping. Carbon, 2014, 77, 492-500.	10.3	48
22	Stable and metastable Si negative-U centers in AlGaN and AlN. Applied Physics Letters, 2014, 105, .	3.3	47
23	Raman and IR study of cobalt acetate dihydrate. Journal of Molecular Structure, 1995, 354, 119-125.	3.6	46
24	Lateral Enlargement Growth Mechanism of 3C-SiC on Off-Oriented 4H-SiC Substrates. Crystal Growth and Design, 2014, 14, 6514-6520.	3.0	46
25	MOCVD of AlN on epitaxial graphene at extreme temperatures. CrystEngComm, 2021, 23, 385-390.	2.6	46
26	High-Quality 2'' Bulk-Like Free-Standing GaN Grown by HydrideVapour Phase Epitaxy on a Si-doped Metal Organic Vapour Phase Epitaxial GaN Template with an Ultra Low Dislocation Density. Japanese Journal of Applied Physics, 2005, 44, 1181-1185.	1.5	45
27	Excitation properties of the divacancy in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi><mml:mo></mml:mo></mml:mrow></mml:math> -SiC. Physical Review B, 2018, 98, .	3.2	44
28	CFx thin solid films deposited by high power impulse magnetron sputtering: Synthesis and characterization. Surface and Coatings Technology, 2011, 206, 646-653.	4.8	43
29	Fast growth of high quality GaN. Physica Status Solidi A, 2003, 200, 13-17.	1.7	42
30	Phonon replicas at theMpoint in4Hâ^'SiC:A theoretical and experimental study. Physical Review B, 1998, 58, 13634-13647.	3.2	39
31	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. Crystal Growth and Design, 2015, 15, 2940-2947.	3.0	38
32	Vibrational modifications on lithium intercalation in V2O5 films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 33, 168-172.	3.5	36
33	Contribution of free-electron recombination to the luminescence spectra of thick GaN films grown by hydride vapor phase epitaxy. Journal of Applied Physics, 1999, 85, 7888-7892.	2.5	34
34	Defects in N, O and N, Zn implanted ZnO bulk crystals. Journal of Applied Physics, 2013, 113, .	2.5	34
35	Real-time sensing of lead with epitaxial graphene-integrated microfluidic devices. Sensors and Actuators B: Chemical, 2019, 288, 425-431.	7.8	34
36	Graphene self-switching diodes as zero-bias microwave detectors. Applied Physics Letters, 2015, 106, .	3.3	33

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37	Atomic layer deposition of InN using trimethylindium and ammonia plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	2.1	33
38	Ga-bound excitons in 3C-, 4H-, and 6H-SiC. Physical Review B, 1996, 53, 13503-13506.	3.2	32
39	Direct observation of large-scale nonuniformities in hydride vapor-phase epitaxy-grown gallium nitride by cathodoluminescence. Applied Physics Letters, 1998, 73, 3583-3585.	3.3	32
40	Vibrational studies of copper thiogallate solid solutions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 57, 102-109.	3.5	32
41	The material quality of CVD-grown SiC using different carbon precursors. Journal of Crystal Growth, 1998, 183, 163-174.	1.5	31
42	Analysis of the sharp donor-acceptor pair luminescence in4H-SiC doped with nitrogen and aluminum. Physical Review B, 2003, 67, .	3.2	31
43	Uniform hot-wall MOCVD epitaxial growth of 2inch AlGaN/GaN HEMT structures. Journal of Crystal Growth, 2007, 300, 100-103.	1.5	30
44	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. Applied Physics Letters, 2002, 81, 2196-2198.	3.3	29
45	Considerably long carrier lifetimes in high-quality 3C-SiC(111). Applied Physics Letters, 2012, 100, .	3.3	29
46	The growth of V2O5 flash-evaporated films. Journal of Materials Science Letters, 1995, 14, 934-936.	0.5	27
47	Highâ€resolution xâ€ray analysis of InGaN/GaN superlattices grown on sapphire substrates with GaN layers. Applied Physics Letters, 1996, 69, 3390-3392.	3.3	27
48	Characterization of the ternary compounds AgGaTe2 and AgGa5Te8. Journal of Materials Science, 1996, 31, 3315-3319.	3.7	27
49	In-grown stacking faults in 4H-SiC epilayers grown on off-cut substrates. Journal of Applied Physics, 2009, 105, .	2.5	27
50	Reduction of structural defects in thick 4H-SiC epitaxial layers grown on 4Â° off-axis substrates. Journal of Applied Physics, 2013, 113, .	2.5	26
51	In Situ Activation of an Indium(III) Triazenide Precursor for Epitaxial Growth of Indium Nitride by Atomic Layer Deposition. Chemistry of Materials, 2020, 32, 4481-4489.	6.7	26
52	Raman study of complexation in aqueous solutions of magnesium acetate. Journal of Molecular Structure, 1996, 377, 13-17.	3.6	25
53	Performance tuning of gas sensors based on epitaxial graphene on silicon carbide. Materials and Design, 2018, 153, 153-158.	7.0	25
54	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties ofGaNxP1â^'xalloys: A proof for a general property of dilute nitrides. Physical Review B, 2004, 70, .	3.2	24

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55	Surface functionalization of epitaxial graphene on SiC by ion irradiation for gas sensing application. Applied Surface Science, 2017, 403, 707-716.	6.1	24
56	Seedâ€Layerâ€Free Atomic Layer Deposition of Highly Uniform Al₂O₃ Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. Advanced Materials Interfaces, 2019, 6, 1900097.	3.7	24
57	Process stability and morphology optimization of very thick 4Hâ€“SiC epitaxial layers grown by chloride-based CVD. Journal of Crystal Growth, 2013, 380, 55-60.	1.5	23
58	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. Carbon, 2017, 116, 722-732.	10.3	23
59	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. Scientific Reports, 2017, 7, 5151.	3.3	23
60	Probing the uniformity of hydrogen intercalation in quasi-free-standing epitaxial graphene on SiC by micro-Raman mapping and conductive atomic force microscopy. Nanotechnology, 2019, 30, 284003.	2.6	23
61	Defects in SiC. Physica B: Condensed Matter, 2003, 340-342, 15-24.	2.7	22
62	Rolling performance of carbon nitride-coated bearing components in different lubrication regimes. Tribology International, 2017, 114, 141-151.	5.9	22
63	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. Journal of Electronic Materials, 2004, 33, 389-394.	2.2	20
64	A comparative study of direct current magnetron sputtering and high power impulse magnetron sputtering processes for CNx thin film growth with different inert gases. Diamond and Related Materials, 2016, 64, 13-26.	3.9	20
65	The growth and electrochemical properties of V6O13 flash-evaporated films. Solid State Ionics, 1995, 76, 133-141.	2.7	19
66	The Endocyclic Carbon Substituent of Guanidinate and Amidinate Precursors Controlling Atomic Layer Deposition of InN Films. Journal of Physical Chemistry C, 2019, 123, 25691-25700.	3.1	19
67	Recombination centers in as-grown and electron-irradiated ZnO substrates. Journal of Applied Physics, 2007, 102, 093504.	2.5	18
68	On the use of methane as a carbon precursor in Chemical Vapor Deposition of silicon carbide. Journal of Crystal Growth, 2014, 390, 24-29.	1.5	18
69	Monitoring of epitaxial graphene anodization. Electrochimica Acta, 2017, 238, 91-98.	5.2	18
70	Lead (Pb) interfacing with epitaxial graphene. Physical Chemistry Chemical Physics, 2018, 20, 17105-17116.	2.8	18
71	Optical and Electrical Properties of Ga2Te3 Crystals. Physica Status Solidi A, 1994, 145, 207-215.	1.7	17
72	CVD Growth and Characterisation of SiC Epitaxial Layers on Faces Perpendicular to the (0001) Basal Plane. Materials Science Forum, 1998, 264-268, 123-126.	0.3	17

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73	Optical selection rules for shallow donors in4Hâˆ’SiCand ionization energy of the nitrogen donor at the hexagonal site. Physical Review B, 2003, 67, .	3.2	17
74	Reactive high power impulse magnetron sputtering of CFx thin films in mixed Ar/CF4 and Ar/C4F8 discharges. Thin Solid Films, 2013, 542, 21-30.	1.8	17
75	Low-temperature growth of low friction wear-resistant amorphous carbon nitride thin films by mid-frequency, high power impulse, and direct current magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	17
76	Energy levels and charge state control of the carbon antisite-vacancy defect in 4H-SiC. Applied Physics Letters, 2019, 114, .	3.3	17
77	Effect of epitaxial graphene morphology on adsorption of ambient species. Applied Surface Science, 2019, 486, 239-248.	6.1	17
78	Quasi-free-standing monolayer and bilayer graphene growth on homoepitaxial on-axis 4H-SiC(0 0 0 1) layers. Carbon, 2015, 82, 12-23.	10.3	16
79	A comparative study of high-quality C-face and Si-face 3C-SiC(1â€‰1â€‰1) grown on off-oriented 4H-SiC substrates. Journal Physics D: Applied Physics, 2019, 52, 345103.	2.8	16
80	Raman probing of hydrogen-intercalated graphene on Si-face 4H-SiC. Materials Science in Semiconductor Processing, 2019, 96, 145-152.	4.0	16
81	Charge state control of the silicon vacancy and divacancy in silicon carbide. Journal of Applied Physics, 2021, 129, .	2.5	16
82	High Growth Rate of Î±-SiC by Sublimation Epitaxy. Materials Science Forum, 1998, 264-268, 143-146.	0.3	15
83	Homoepitaxial On-Axis Growth of 4H- and 6H-SiC by CVD. Materials Science Forum, 2004, 457-460, 193-196.	0.3	15
84	Large-area free-standing GaN substrate grown by hydride vapor phase epitaxy on epitaxial lateral overgrown GaN template. Physica B: Condensed Matter, 2006, 371, 133-139.	2.7	15
85	Surface functionalization of epitaxial graphene using ion implantation for sensing and optical applications. Carbon, 2020, 157, 169-184.	10.3	15
86	Spin-relaxation times exceeding seconds for color centers with strong spinâ€“orbit coupling in SiC. New Journal of Physics, 2020, 22, 103051.	2.9	15
87	Exciton dynamics in homoepitaxial GaN. Solid State Communications, 1997, 104, 205-209.	1.9	14
88	EPR and ENDOR Studies of Shallow Donors in SiC. Applied Magnetic Resonance, 2010, 39, 49-85.	1.2	14
89	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. Physica B: Condensed Matter, 2012, 407, 1462-1466.	2.7	14
90	Silicon carbonitride thin films deposited by reactive high power impulse magnetron sputtering. Surface and Coatings Technology, 2018, 335, 248-256.	4.8	14

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91	Elimination of step bunching in the growth of large-area monolayer and multilayer graphene on off-axis 3C SiC (111). Carbon, 2018, 140, 533-542.	10.3	14
92	A SIMS study on Mg diffusion in Zn0.94Mg0.06O/ZnO heterostructures grown by metal organic chemical vapor deposition. Applied Surface Science, 2011, 257, 8629-8633.	6.1	13
93	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. Journal of Physics Condensed Matter, 2013, 25, 335804.	1.8	13
94	Experimental study of the effect of local atomic ordering on the energy band gap of melt grown InGaAsN alloys. Semiconductor Science and Technology, 2017, 32, 085005.	2.0	13
95	Ligand hyperfine interactions at silicon vacancies in 4H-SiC. Journal of Physics Condensed Matter, 2019, 31, 195501.	1.8	13
96	Reactive sputtering of CSx thin solid films using CS2 as precursor. Vacuum, 2020, 182, 109775.	3.5	13
97	Growth and Characterisation of Thick SiC Epilayers by High Temperature CVD. Materials Science Forum, 1998, 264-268, 103-106.	0.3	12
98	Micro-Raman scattering profiling studies on HVPE-grown free-standing GaN. Physica Status Solidi A, 2004, 201, 2773-2776.	1.7	12
99	High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure ²⁸Si¹²C, Natural and ¹³C â€“ Enriched 4H-SiC. Materials Science Forum, 0, 778-780, 471-474.	0.3	12
100	Resonant sharp hot free-exciton luminescence in 6H- and 4H-SiC due to inhibited exciton-phonon interaction. Physical Review B, 2001, 64, .	3.2	11
101	Temperature-Dependent Hall Effect Measurements in Low â€“ Compensated p-Type 4H-SiC. Materials Science Forum, 2004, 457-460, 677-680.	0.3	11
102	Trimethylboron as Single-Source Precursor for Boronâ€“Carbon Thin Film Synthesis by Plasma Chemical Vapor Deposition. Journal of Physical Chemistry C, 2016, 120, 21990-21997.	3.1	11
103	Calibration on wide-ranging aluminum doping concentrations by photoluminescence in high-quality uncompensated p-type 4H-SiC. Applied Physics Letters, 2017, 111, .	3.3	11
104	Understanding Graphene Response to Neutral and Charged Lead Species: Theory and Experiment. Materials, 2018, 11, 2059.	2.9	11
105	Direct epitaxial nanometer-thin InN of high structural quality on 4Hâ€“SiC by atomic layer deposition. Applied Physics Letters, 2020, 117, .	3.3	11
106	Thick GaN Layers Grown on A-plane Sapphire Substrates by Hydride Vapour Phase Epitaxy. Physica Scripta, 1999, T79, 67.	2.5	10
107	Excitation properties of hydrogen-related photoluminescence in6Hâ^'SiC. Physical Review B, 2000, 62, 7162-7168.	3.2	10
108	Optical and morphological features of bulk and homoepitaxial ZnO. Superlattices and Microstructures, 2006, 39, 247-256.	3.1	10

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109	Surface engineering of SiC via sublimation etching. Applied Surface Science, 2016, 390, 816-822.	6.1	10
110	CVD growth and properties of on-axis vanadium doped semi-insulating 4H-SiC epilayers. Journal of Applied Physics, 2019, 125, .	2.5	10
111	Probing the uniformity of silver-doped epitaxial graphene by micro-Raman mapping. Physica B: Condensed Matter, 2020, 580, 411751.	2.7	10
112	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. ACS Applied Nano Materials, 2021, 4, 1282-1293.	5.0	10
113	High quality 4H-SiC grown on various substrate orientations. Diamond and Related Materials, 1997, 6, 1289-1292.	3.9	9
114	Metastability of a Hydrogen-related Defect in 6H-SiC. Materials Science Forum, 2000, 338-342, 651-654.	0.3	9
115	Highly homogeneous bulk-like 2â€²â€² GaN grown by HVPE on MOCVDâ€“GaN template. Journal of Crystal Growth, 2005, 275, e387-e393.	1.5	9
116	Negative-U behavior of the Si donor in Al0.77Ga0.23N. Applied Physics Letters, 2013, 103, 042101.	3.3	9
117	Brominated Chemistry for Chemical Vapor Deposition of Electronic Grade SiC. Chemistry of Materials, 2015, 27, 793-801.	6.7	9
118	Exploring the Interface Landscape of Noble Metals on Epitaxial Graphene. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000673.	1.8	9
119	Layer quality of Sb-doped GaAs grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1993, 129, 143-148.	1.5	8
120	Exciton Dynamics in Homoepitaxial GaN. Materials Science Forum, 1998, 264-268, 1275-1278.	0.3	8
121	Zeeman spectroscopy of the D1 bound exciton in 3Câ€“, and 4Hâ€“SiC. Physica B: Condensed Matter, 1999, 273-274, 677-680.	2.7	8
122	SiC and III-Nitride Growth in Hot-Wall CVD Reactor. Materials Science Forum, 2005, 483-485, 61-66.	0.3	8
123	Effective-mass approximation for shallow donors in uniaxial indirect band-gap crystals and application to4Hâ^'SiC. Physical Review B, 2006, 73, .	3.2	8
124	Control of Epitaxial Graphene Thickness on 4H-SiC(0001) and Buffer Layer Removal through Hydrogen Intercalation. Materials Science Forum, 0, 717-720, 605-608.	0.3	8
125	Surface photovoltage and photoluminescence study of thick Ga(In)AsN layers grown by liquid-phase epitaxy. Journal of Physics: Conference Series, 2016, 700, 012028.	0.4	8
126	Modified Epitaxial Graphene on SiC for Extremely Sensitive and Selective Gas Sensors. Materials Science Forum, 2016, 858, 1145-1148.	0.3	8

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127	Phonons in polymorphous PbTe films. II. Infrared and Raman spectra of PbTe and PbTe:Cr films on KCl substrates. Journal of Physics Condensed Matter, 1992, 4, 4645-4652.	1.8	7
128	High-temperature excitons in GaAs quantum wells embedded in AlAs/GaAs superlattices. Vacuum, 2000, 58, 478-484.	3.5	7
129	Anti-site pair in SiC: a model of the DI center. Physica B: Condensed Matter, 2003, 340-342, 175-179.	2.7	7
130	Effective-Mass Theory of Shallow Donors in 4H-SiC. Materials Science Forum, 2005, 483-485, 511-514.	0.3	7
131	Ionization energy of the phosphorus donor in 3Câ€“SiC from the donor-acceptor pair emission. Journal of Applied Physics, 2010, 108, .	2.5	7
132	Assessment of H-intercalated graphene for microwave FETs through material characterization and electron transport studies. Carbon, 2015, 81, 96-104.	10.3	7
133	Excitonic emission in heavily Ga-doped zinc oxide films grown on GaN. Journal of Luminescence, 2020, 223, 117265.	3.1	7
134	Cathodoluminescence of Defect Regions in SiC Epi-Films. Materials Science Forum, 1998, 264-268, 653-656.	0.3	6
135	B implantation in 6Hâ€“SiC: Lattice damage recovery and implant activation upon high-temperature annealing. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1040.	1.6	6
136	Photoluminescence of 4H-SiC: some remarks. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 234-238.	3.5	6
137	Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells. Thin Solid Films, 2000, 364, 224-227.	1.8	6
138	Excitation spectra of nitrogen bound excitons in 4H- and 6H-SiC. Journal of Applied Physics, 2002, 91, 2028-2032.	2.5	6
139	Photoconductivity of Lightly-Doped and Semi-Insulating 4H-SiC and the Free Exciton Binding Energy. Materials Science Forum, 2002, 389-393, 613-616.	0.3	6
140	Characterization of crack-free relaxed GaN grown on 2â€³ sapphire. Journal of Applied Physics, 2005, 98, 073525.	2.5	6
141	Splitting of type-I (N-B, P-Al) and type-II (N-Al, N-Ga) donor-acceptor pair spectra in 3C-SiC. Physical Review B, 2011, 83, .	3.2	6
142	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. Physical Review B, 2015, 92, .	3.2	6
143	Light emission enhancement from ZnO nanostructured films grown on Gr/SiC substrates. Carbon, 2016, 99, 295-301.	10.3	6
144	Interplay between thin silver films and epitaxial graphene. Surface and Coatings Technology, 2020, 381, 125200.	4.8	6

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145	Growth of 4H-SiC from liquid phase. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 329-332.	3.5	5
146	The D1 Exciton in 4H-SiC. Physica Status Solidi (B): Basic Research, 1998, 210, 337-340.	1.5	5
147	Changes in the Exciton-Related Photoluminescence of 4H- and 6H-SiC Induced by Uniaxial Stress. Materials Science Forum, 1998, 264-268, 489-492.	0.3	5
148	Pseudo-Donors in SiC. Materials Science Forum, 2000, 338-342, 647-650.	0.3	5
149	Influence of dislocation density on photoluminescence intensity of GaN. Journal of Crystal Growth, 2005, 278, 406-410.	1.5	5
150	Deep levels related to the carbon antisiteâ€“vacancy pair in 4H-SiC. Journal of Applied Physics, 2021, 130, .	2.5	5
151	Fluorescence spectrum and charge state control of divacancy qubits via illumination at elevated temperatures in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>4</mml:mn><mml:mi>H</mml:mi></mml:mrow></mml silicon carbide. Physical Review B, 2022, 105, .	3.2	5
152	Photoluminescence excitation spectra of the free exciton emission in 6Hâ€“SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 265-269.	3.5	4
153	Characterization of High-Quality Free-Standing GaN Grown by HVPE. Physica Scripta, 2004, T114, 18-21.	2.5	4
154	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. Journal of Crystal Growth, 2008, 310, 1006-1009.	1.5	4
155	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study. , 2014, , .		4
156	Growth optimization and applicability of thick on-axis SiC layers using sublimation epitaxy in vacuum. Journal of Crystal Growth, 2016, 448, 51-57.	1.5	4
157	Optical properties of thick GaInAs(Sb)N layers grown by liquid-phase epitaxy. Journal of Physics: Conference Series, 2017, 794, 012013.	0.4	4
158	Resolving mobility anisotropy in quasi-free-standing epitaxial graphene by terahertz optical Hall effect. Carbon, 2021, 172, 248-259.	10.3	4
159	Bidirectional Hydrogen Electrocatalysis on Epitaxial Graphene. ACS Omega, 2022, 7, 13221-13227.	3.5	4
160	Spectral Behavior of Zeroâ€Bias Photocurrent at Low Temperature in Bulk Semiâ€Insulating GaAsâ€‰:â€‰Cr. Journal of the Electrochemical Society, 1994, 141, 2533-2536.	2.9	3
161	Optical characterization of MBE-grown GaNAs. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 50, 153-156.	3.5	3
162	Some Aspects of the Photoluminescence and Raman Spectroscopy of (10-10)- and (11-20)-Oriented 4H and 6H Silicon Carbide. Materials Science Forum, 1998, 264-268, 469-472.	0.3	3

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163	Effect of non-abrupt interfaces in AlAs/GaAs superlattices with embedded GaAs quantum wells. Vacuum, 2000, 58, 561-567.	3.5	3
164	Photoluminescence line-shape analysis in quantum wells embedded in superlattices. Materials Science and Engineering C, 2001, 15, 75-77.	7.3	3
165	Photoluminescence upconversion in 4Hâ€“SiC. Applied Physics Letters, 2002, 81, 2547-2549.	3.3	3
166	Chloride-based SiC growth on a-axis 4Hâ€“SiC substrates. Physica B: Condensed Matter, 2016, 480, 23-25.	2.7	3
167	Defects in silicon carbide grown by fluorinated chemical vapor deposition chemistry. Physica B: Condensed Matter, 2018, 535, 44-49.	2.7	3
168	Critical View on Buffer Layer Formation and Monolayer Graphene Properties in High-Temperature Sublimation. Applied Sciences (Switzerland), 2021, 11, 1891.	2.5	3
169	Understanding of the Electrochemical Behavior of Lithium at Bilayer-Patched Epitaxial Graphene/4H-SiC. Nanomaterials, 2022, 12, 2229.	4.1	3
170	Modified divacancies in 4H-SiC. Journal of Applied Physics, 2022, 132, .	2.5	3
171	Near Band-Gap Emission in V-Implanted and Annealed 4H-SiC. Materials Science Forum, 1998, 264-268, 497-500.	0.3	2
172	Bound Exciton Recombination in Electron Irradiated 4H-SiC. Materials Science Forum, 1998, 264-268, 477-480.	0.3	2
173	Domain Structure of Thick GaN Layers Grown by Hydride Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	2
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